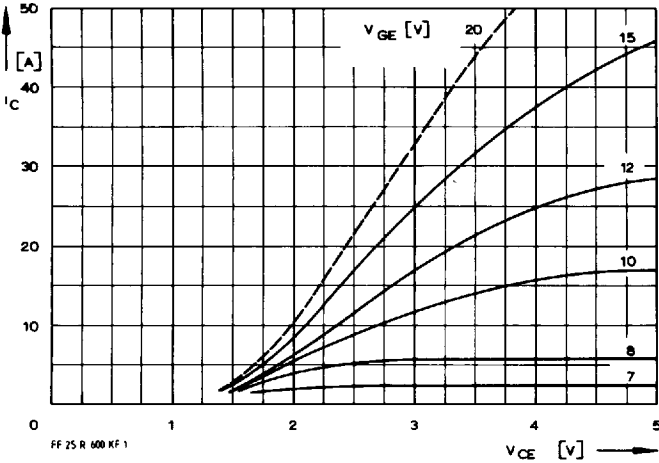
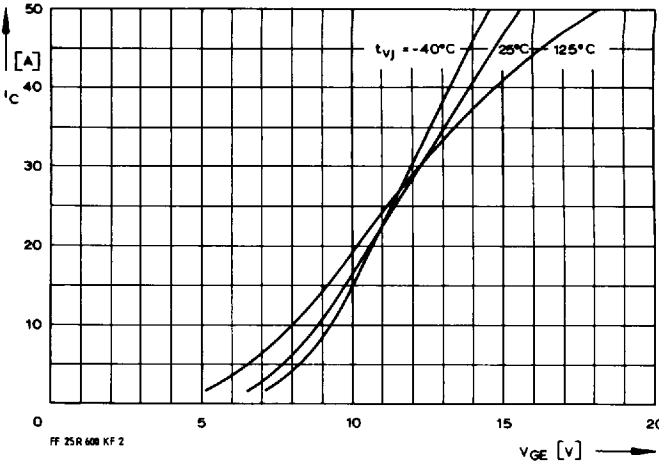


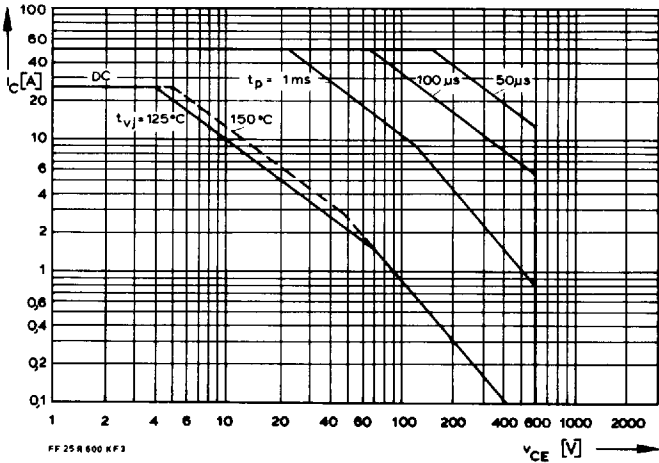
Transistor				Thermische Eigenschaften		Thermal properties	
Elektrische Eigenschaften				Electrical properties		Electrical properties	
Höchstzulässige Werte				Maximum rated values		Maximum rated values	
V _{CES}			600	V	R _{thJC}	DC, pro Baustein / per module	0,5 °C/W
I _C			25	A		DC, pro Zweig / per arm	1 °C/W
I _{CRM}		t _p = 1 ms	50	A	R _{thCK}	pro Baustein / per module	0,065 °C/W
P _{tot}		t _C = 25°C	125	W		pro Zweig / per arm	0,13 °C/W
V _{GE}			20	V	t _{vjmax}		150 °C
V _{EG}			20	V	t _{vjop}		-40 / + 150 °C
					t _{stg}		-40 / + 125 °C
Charakteristische Werte				Characteristic values		Inverse diode	
V _{CE sat}		i _{CM} = 25 A, v _{GE} = 15 V, t _{vj} = 25°C	typ.	3	V	Inverse diode	
		i _{CM} = 25 A, v _{GE} = 15 V, t _{vj} = 25°C	max.	4	V	Electrical properties	
V _{GE (th)}		v _{CE} = 5 V, i _C = 25 mA, t _{vj} = 25°C	min.	3	V	Electrical properties	
		v _{CE} = 5 V, i _C = 25 mA, t _{vj} = 25°C	max.	6	V	Electrical properties	
C _{GE}		v _{CE} = 10 V, v _{GE} = 0 V, f _o = 1 MHz, t _{vj} = 25°C	typ.	1,4	nF	Electrical properties	
i _{CES}		v _{CE} = 600 V, v _{GE} = 0 V, t _{vj} = 25°C	typ.	0,2	mA	Electrical properties	
		v _{CE} = 600 V, v _{GE} = 0 V, t _{vj} = 125°C	typ.	1	mA	Electrical properties	
i _{GES}		v _{GE} = 20 V, t _{vj} = 25°C	typ.	50	nA	Electrical properties	
		v _{GE} = 20 V, t _{vj} = 25°C	max.	500	nA	Electrical properties	
i _{EGS}		v _{EG} = 20 V, t _{vj} = 25°C	typ.	50	nA	Electrical properties	
		v _{EG} = 20 V, t _{vj} = 25°C	max.	500	nA	Electrical properties	
t _{on}		i _{CM} = 25 A, v _{CE} = 300 V, v _{LF} = 15 V, R _G = 100 Ω, t _{vj} = 25°C	typ.	0,4	μs	Electrical properties	
		i _{CM} = 25 A, v _{CE} = 300 V, v _{LF} = 15 V, R _G = 100 Ω, t _{vj} = 125°C	typ.	0,5	μs	Electrical properties	
t _s		i _{CM} = 25 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 100 Ω, t _{vj} = 25°C	typ.	0,4	μs	Electrical properties	
		i _{CM} = 25 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 100 Ω, t _{vj} = 125°C	typ.	0,5	μs	Electrical properties	
t _f		i _{CM} = 25 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 100 Ω, t _{vj} = 25°C	typ.	0,15	μs	Electrical properties	
		i _{CM} = 25 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 100 Ω, t _{vj} = 125°C	typ.	0,25	μs	Electrical properties	
Bedingungen für den Kurzschlußschutz				Conditions for protection against short circuits		Internal insulation	
						Insulating material: AlN	
						2,5 kV	



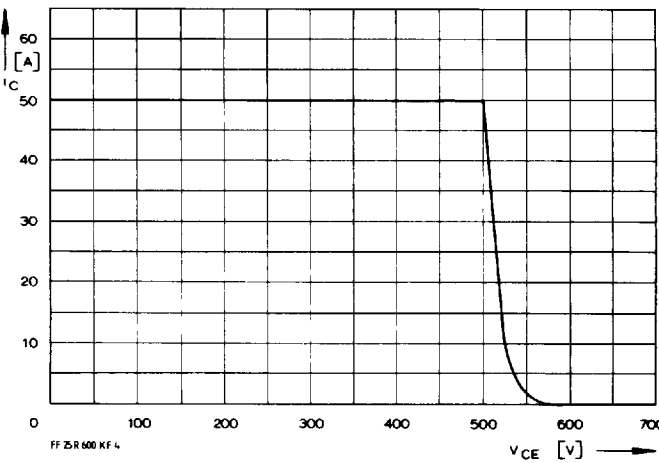
1 Kollektor-Emitter-Spannung im Sättigungsbereich (typisch).
Collector-emitter-voltage in saturation region (typical).
 $t_{vj} = 25^{\circ}\text{C}$



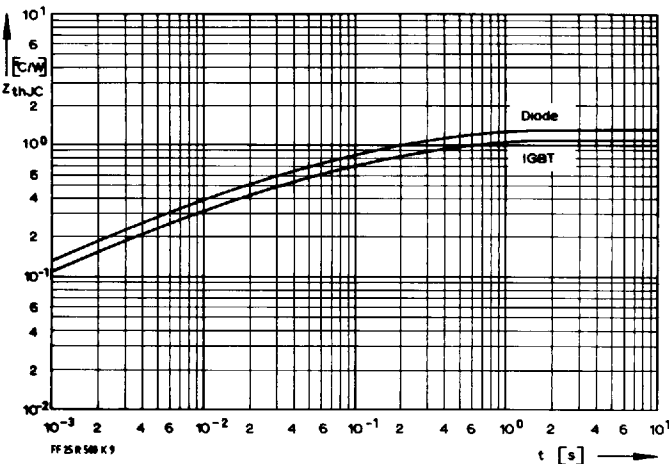
2 Übertragungscharakteristik (typisch).
Transfer characteristic (typical).
 $V_{CE} = 5\text{ V}$



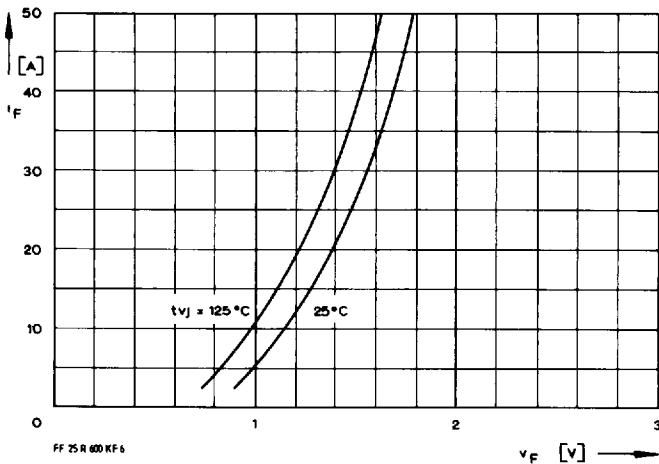
3 Erlaubter Arbeitsbereich in Vorwärtsrichtung (Einzelimpuls, nicht periodisch).
Forward biased safe operating area (single pulse, non repetitive).
 $t_C = 25^{\circ}\text{C}$



4 Erlaubter Arbeitsbereich in Rückwärtsrichtung.
Reverse biased safe operating area.
 $t_{vj} = 125^{\circ}\text{C}$, $V_{LF} = V_{LR} = 15\text{ V}$, $R_G = 100\ \Omega$



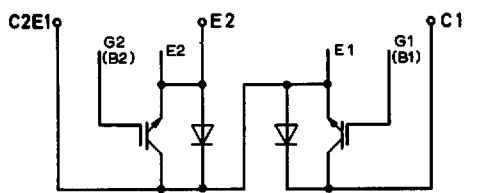
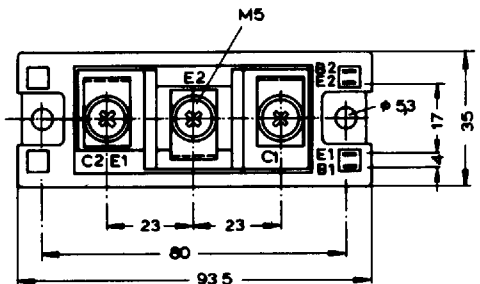
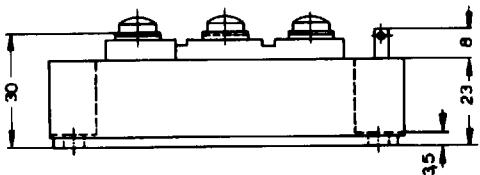
5 Transienter innerer Wärmewiderstand je Zweig (DC).
Transient thermal impedance per arm (DC).



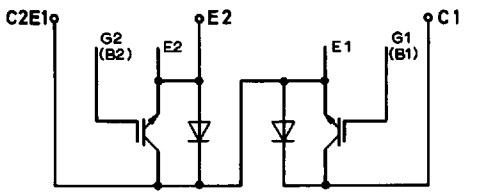
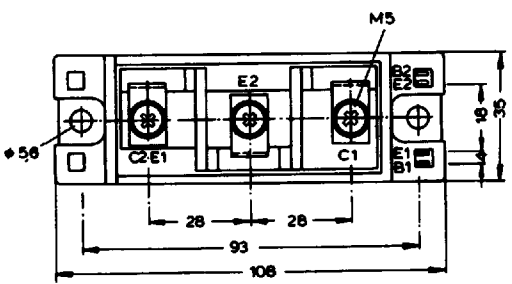
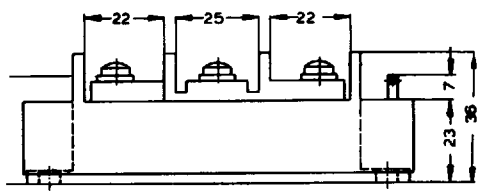
6 Durchlaßkennlinie der Inversdiode (typisch).
Forward characteristic of the inverse diode (typical).
 $V_{GE} = 0\text{ V}$

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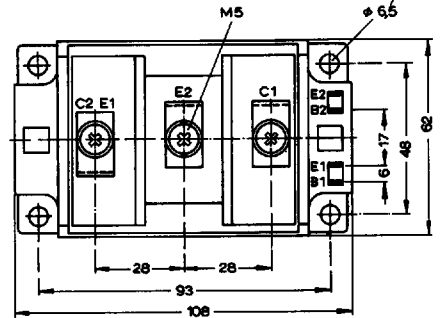
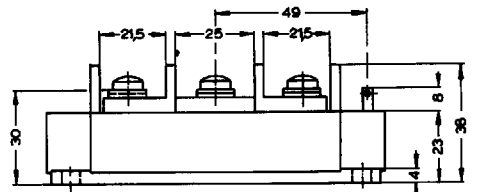
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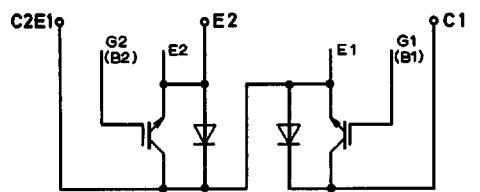
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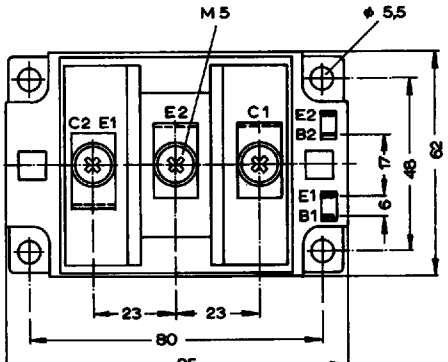
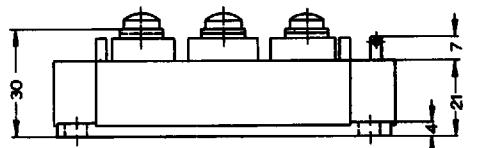


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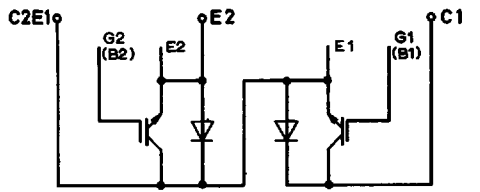


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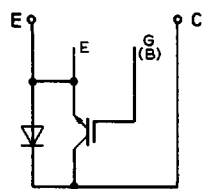
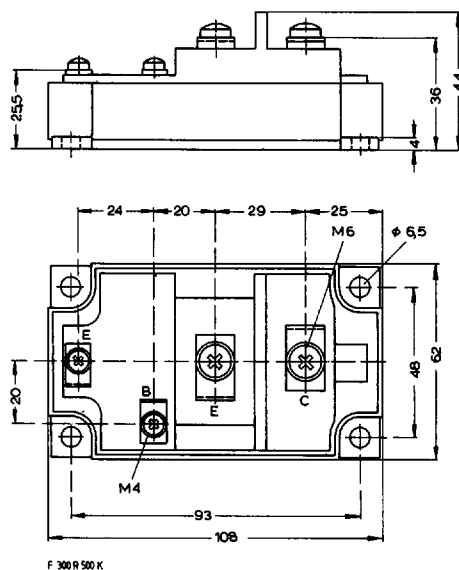
FF 150 R 500 K



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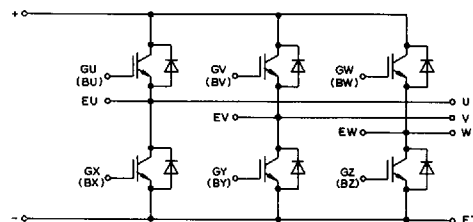
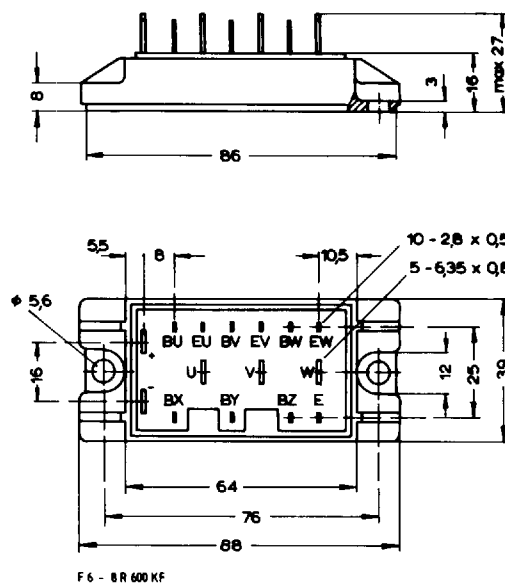
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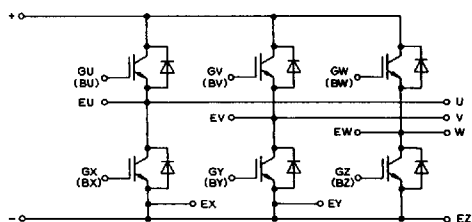
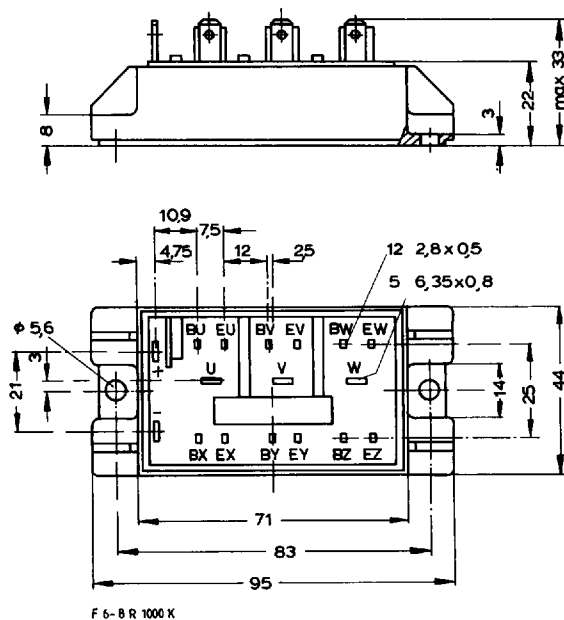


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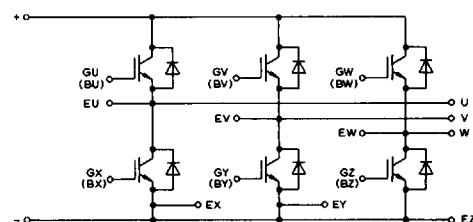
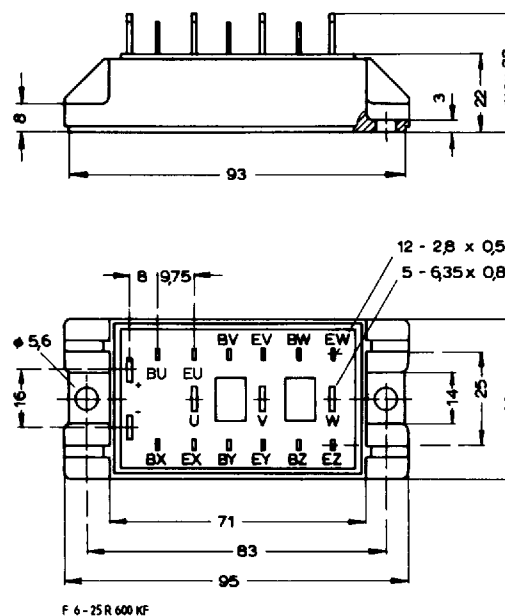
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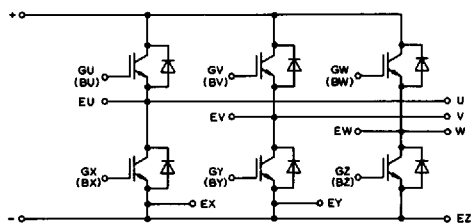
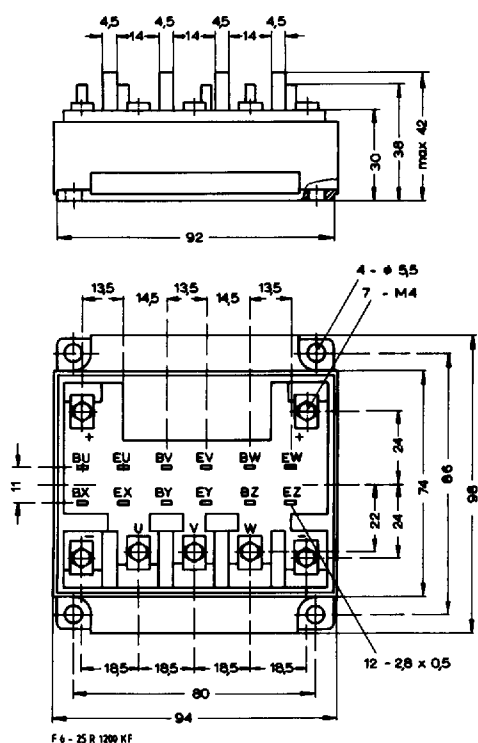
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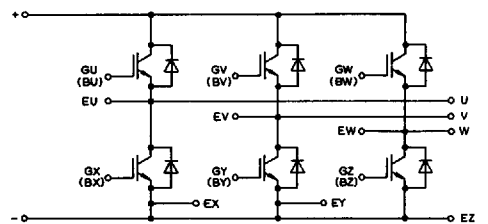
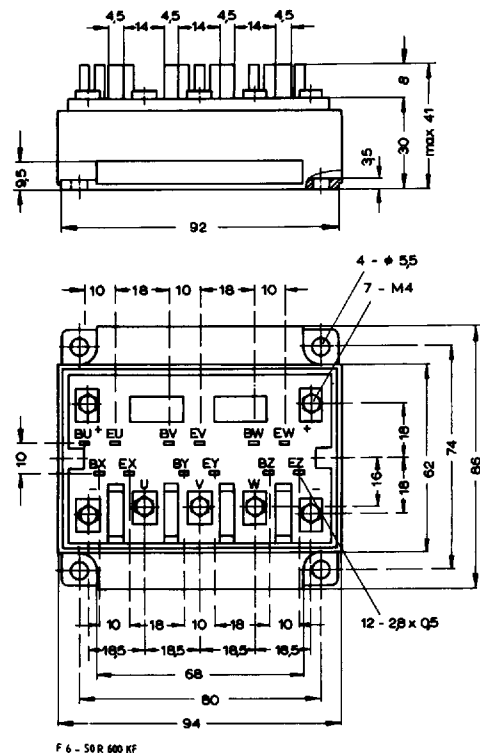
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